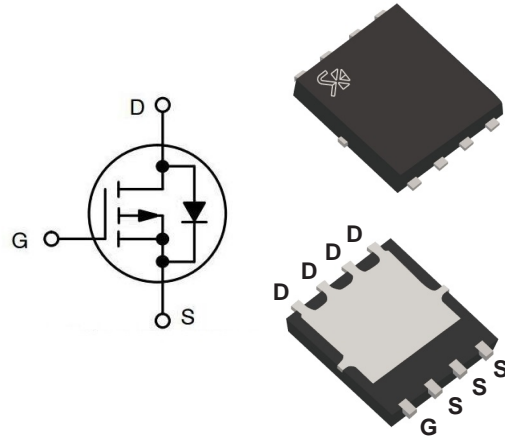


Feature

- 20V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- $R_{DS(ON)} = 6m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- $R_{DS(ON)} = 7.5m\Omega$ (typ.) @ $V_{GS} = -2.5V$
- Reliable and Rugged.

Applications

- Power Management in Notebook Computer, and Portable Equipment and Battery Systems.



PDFN5060

Electrical Characteristics

1. Absolute Maximum Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	
I_D	Continue Drain Current	-40	A
I_{DM}	Pulsed Drain Current	-160	
I_S	Diode Continuous Forward Current	-40	A
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	

2. Static Electrical Characteristics ($T_A = 25^\circ C$ Unless Otherwise Noted)

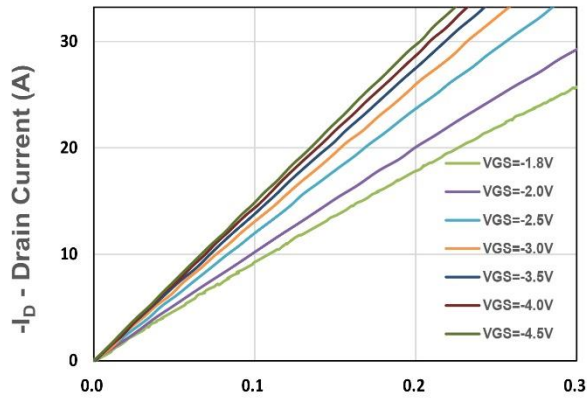
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{DS} = -250\mu A$	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$ $T_J = 85^\circ C$			-1 -30	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.4	-0.6	-0.8	V
I_{GSS}	Gate Body Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS} = -4.5V, I_{DS} = -2A$ $V_{GS} = -2.5V, I_{DS} = -2A$		6 7.5	8 9	$m\Omega$
V_{SD}	Diode Forward Voltage	$I_{SD} = -2A, V_{GS} = 0V$		-0.6	-1.3	V

*Note:

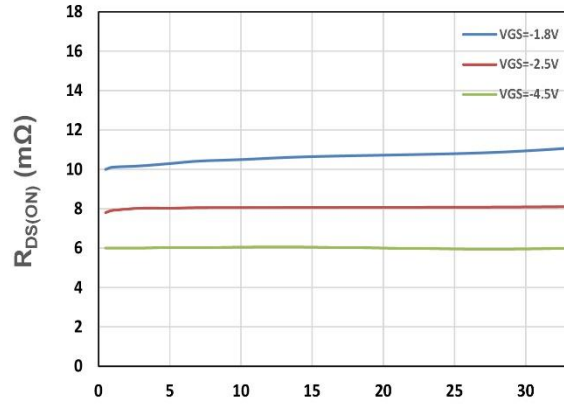
a : Current maybe limit by bonding wire.

b : The $R_{\theta JA}$ is the sum of the thermal impedance from junction to ambient and depend on package type.

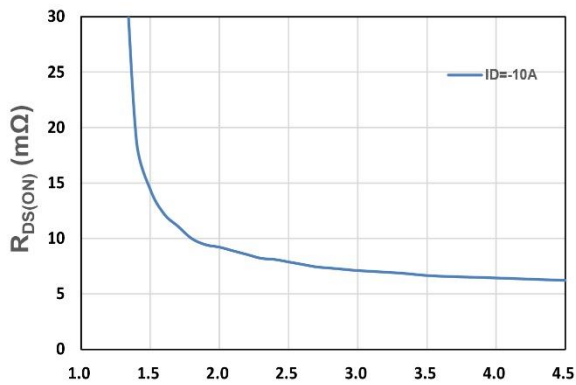
TYPICAL CHARACTERISTICS



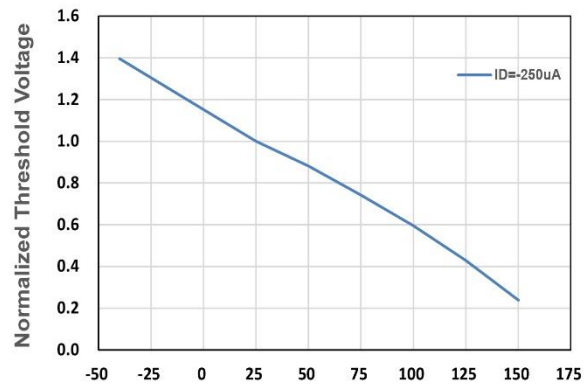
-V_{DS} - Drain - Source Voltage (V)
Figure 1. Output Characteristics



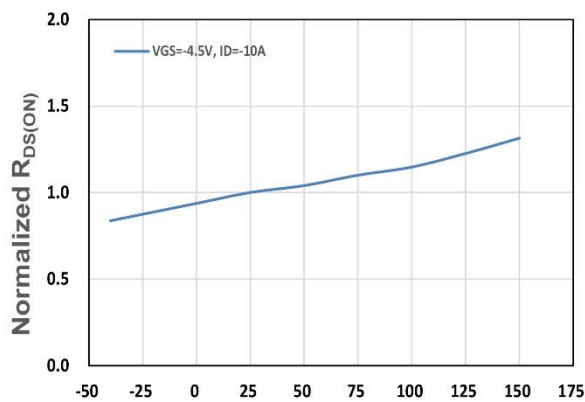
-ID - Drain Current (A)
Figure 2. On-Resistance vs. ID



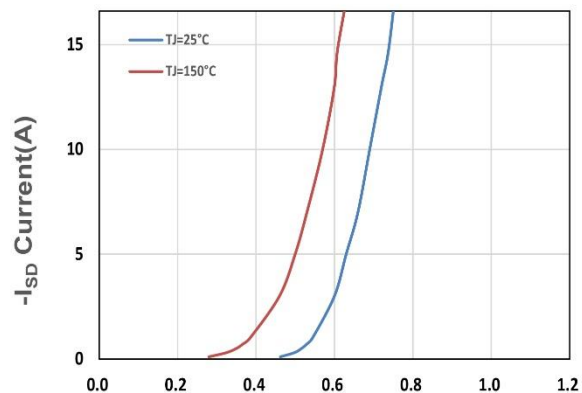
-V_{GS} - Gate - Source Voltage (V)
Figure 3. On-Resistance vs. VGS



T_j, Junction Temperature(°C)
Figure 4. Gate Threshold Voltage



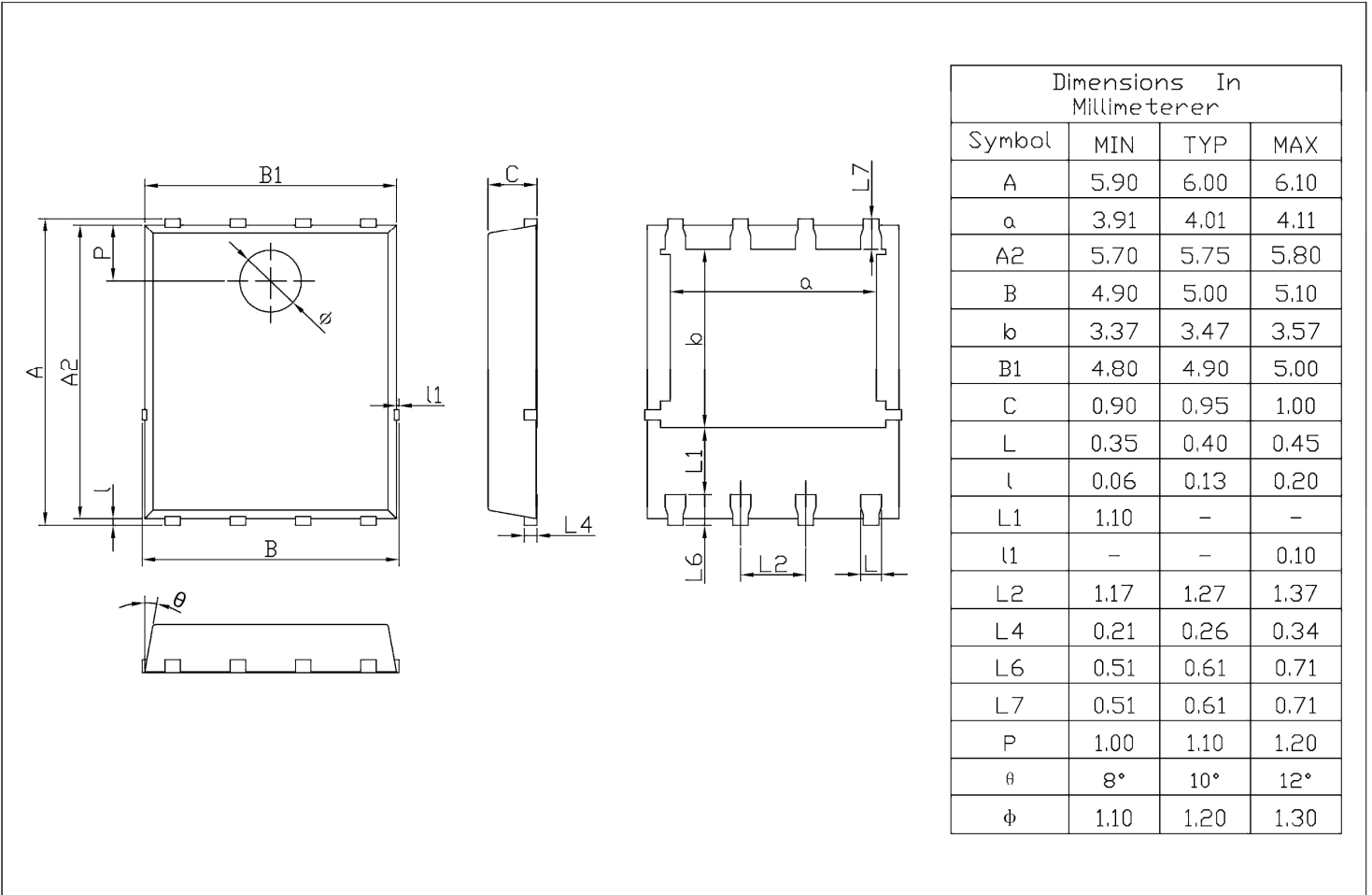
T_j, Junction Temperature(°C)
Figure 5. Drain-Source On Resistance



-V_{SD}, Source-Drain Voltage(V)
Figure 6. Source-Drain Diode Forward

PDFN5060

Unit:mm



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [MOSFET](#) category:

Click to view products by [Shikues](#) manufacturer:

Other Similar products are found below :

[MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [NTNS3A92PZT5G](#) [IRFD120](#) [JANTX2N5237](#) [2N7000](#) [2SK2464-TL-E](#) [AOD464](#) [2SJ277-DL-E](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#) [C3M0021120D](#) [DMN6022SSD-13](#)